

This listing of claims will replace all prior versions of claims in the application.

Claim 1. (previously presented) A process for electroless copper plating comprising:

- 1) depositing a palladium on a resin substrate; and
- 2) treating the resin substrate with a formaldehyde-free electroless copper plating solution, which solution comprises a copper ion and a reducing agent and, wherein no catalyst accelerating treatment is carried out after performing said catalyst depositing treatment.

Claim 2. (previously presented) The process of claim 1 wherein the palladium catalyst is a palladium-tin catalyst.

Claim 3. (currently amended) The process for electroless copper plating according to claim 1 ~~or 2~~ wherein the electroless copper plating solution further comprises a complexing agent.

Claim 4. (currently amended) The process for electroless copper plating according to claim 1 ~~any one of claims 1 through 3~~ wherein the reducing agent is selected from a group consisting of sodium boron hydride, potassium boron hydride, dimethylamino borane, trimethylamino borane, hydrazine, derivatives of these compounds and a mixture thereof.

Claim 5. (currently amended) The process for electroless copper plating according to claim 1 ~~any one of claims 1 to 4~~, wherein the electroless copper plating solution further comprises a water-soluble cerium compound, a water-soluble thallium and/or a water-soluble sulfide.

Claim 6. (currently amended) The process for electroless copper plating according to claim 1 ~~any one of claims 1 to 5~~, wherein the electroless copper plating solution further comprises iodine and/or a water-soluble iodine compound.

Claim 7. (currently amended) The process for electroless copper plating according to claim 1 ~~any one of claims 1 to 6~~, wherein the electroless copper plating solution further comprises hydantoin and/or a hydantoin derivative.

Claim 8. (currently amended) The process for electroless copper plating according to claim 1 ~~any one of claims 1 to 7~~, wherein the deposition rate of copper is 0.05 micrometer/minute or more.

Claim 9. (currently amended) An electroless copper plating solution used in the process for electroless copper plating according to claim 1 ~~any one of claims 1 to 8~~.

Claim 10. (previously presented) An electroless plating system, comprising a resin substrate disposed in a plating solution of claim 9.

Claim 11. (currently amended) A composite material prepared by the process according to claim 1 ~~any one of claims 1 to 8~~.

Claim 12. (previously presented) The composite material according to claim 11, wherein the thickness of the copper layer deposited on the resin substrate is 0.05 micrometer or more.

Claim 13. (currently amended) A process for electro plating copper characterized by further applying an electro copper plating on the composite material according to claim 11 ~~or 12~~.

Claim 14. (previously presented) A composite material prepared by the
process in accordance with claim 13.